

# **isc** Silicon NPN Power Transistor

#### **DESCRIPTION**

- · High DC Current Gain
- Complement to type BD336
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

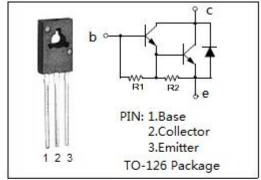
 NPN epitaxial base transistors in monolithic Darlington circuit for audio output stages and general amplifier and switching applications.

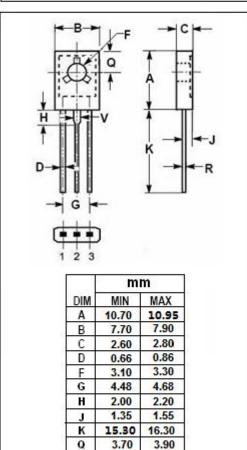
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ic	Collector Current-Continuous	6	А
Івм	Base Current-Peak	0.15	А
Pc	Collector Power Dissipation @ Tc=25°C	60	W
TJ	unction Temperature 150		$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}\!\mathbb{C}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance,Junction to Case	2.08	°C/W
R <sub>th j-a</sub>	R <sub>th j-a</sub> Thermal Resistance,Junction to Ambient		°C/W





0.40

1.17

0.60



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**BD335** 

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

	10-20 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	100			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 12mA			2.0	V			
V <sub>BE(on)</sub>	Base-Emitter On Voltage	Ic= 3A; V <sub>CE</sub> = 3V			2.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0 V <sub>CB</sub> = 100V; I <sub>E</sub> = 0,T <sub>C</sub> =150°C			0.1 1.0	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5	mA			
h <sub>FE-1</sub> *	DC Current Gain	Ic= 0.5A; V <sub>CE</sub> = 3V		1900					
h <sub>FE-2</sub> *	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> =3V	750						
h <sub>FE-3</sub> *	DC Current Gain	I <sub>C</sub> = 6A; V <sub>CE</sub> = 3V		3000					

<sup>\*:</sup>Measured under pulse conditions:tp<300us, \u00f3<2%

#### **NOTICE:**

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